

- ◆ N-Channel Enhancement Mode
- ◆ Low  $Q_g$  and  $R_g$
- ◆ High  $dv/dt$
- ◆ Nanosecond Switching
- ◆ 30MHz Maximum Frequency

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1000	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1\text{ M}\Omega$	1000	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_c = 25^\circ\text{C}$	24	A
$I_{DM}$	$T_c = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	144	A
$I_{AR}$	$T_c = 25^\circ\text{C}$	21	A
$E_{AR}$	$T_c = 25^\circ\text{C}$	30	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 0.2\Omega$	5	V/ns
	$I_S = 0$	>200	V/ns
$P_{DC}$		1800	W
$P_{DHS}$	$T_c = 25^\circ\text{C}$ Derate 4.0W/ $^\circ\text{C}$ above $25^\circ\text{C}$	730	W
$P_{DAMB}$	$T_c = 25^\circ\text{C}$	4.5	W
$R_{thJC}$		0.08	C/W
$R_{thJHS}$		0.20	C/W

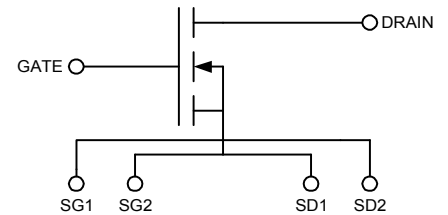
Symbol	Test Conditions	Characteristic Values		
		$T_J = 25^\circ\text{C}$ unless otherwise specified		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 3\text{ ma}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4\text{ ma}$	3.5	4.4	5.5 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8\text{ V}_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0$ , $T_J = 125^\circ\text{C}$			50 $\mu\text{A}$
				1 mA
$R_{DS(on)}$	$V_{GS} = 15\text{ V}$ , $I_D = 0.5I_{D25}$ Pulse test, $t \leq 300\mu\text{s}$ , duty cycle $d \leq 2\%$			0.45 $\Omega$
$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 0.5I_{D25}$ , pulse test		12	S
$T_J$		-55		+175 $^\circ\text{C}$
$T_{JM}$			175	$^\circ\text{C}$
$T_{stg}$		-55		+175 $^\circ\text{C}$
$T_L$	1.6mm (0.063 in) from case for 10 s		300	$^\circ\text{C}$
<b>Weight</b>			3	g

$$V_{DSS} = 1000\text{ V}$$

$$I_{D25} = 24\text{ A}$$

$$R_{DS(on)} \leq 0.45\ \Omega$$

$$P_{DC} = 1800\text{ W}$$


**Features**

- Isolated Substrate
  - high isolation voltage (>2500V)
  - excellent thermal transfer
  - Increased temperature and power cycling capability
- IXYS advanced low  $Q_g$  process
- Low gate charge and capacitances
  - easier to drive
  - faster switching
- Low  $R_{DS(on)}$
- Very low insertion inductance (<2nH)
- No beryllium oxide (BeO) or other hazardous materials

**Advantages**

- Optimized for RF and high speed switching at frequencies to 30MHz
- Easy to mount—no insulators needed
- High power density



# DE475-102N21A RF Power MOSFET

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C unless otherwise specified)		
		min.	typ.	max.
R <sub>G</sub>			0.3	Ω
C <sub>iss</sub>			5500	pF
C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 0.8 V <sub>DSS(max)</sub> , f = 1 MHz		190	pF
C <sub>rss</sub>			52	pF
C <sub>stray</sub>	Back Metal to any Pin		46	pF
T <sub>d(on)</sub>			5	ns
T <sub>on</sub>	V <sub>GS</sub> = 15 V, V <sub>DS</sub> = 0.8 V <sub>DSS</sub> I <sub>D</sub> = 0.5 I <sub>DM</sub>		5	ns
T <sub>d(off)</sub>	R <sub>G</sub> = 0.2 Ω (External)		5	ns
T <sub>off</sub>			8	ns
Q <sub>g(on)</sub>			155	nC
Q <sub>gs</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> I <sub>D</sub> = 0.5 I <sub>D25</sub>		33	nC
Q <sub>gd</sub>			84	nC

Source-Drain Diode		Characteristic Values		
		(T <sub>J</sub> = 25°C unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I <sub>S</sub>	V <sub>GS</sub> = 0 V			21 A
I <sub>SM</sub>	Repetitive; pulse width limited by T <sub>JM</sub>			144 A
V <sub>SD</sub>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2%			1.5 V
T <sub>rr</sub>			200	ns
Q <sub>RM</sub>	I <sub>F</sub> = I <sub>S</sub> , -di/dt = 100A/μs, V <sub>R</sub> = 100V		0.6	μC
I <sub>RM</sub>			8	A

CAUTION: Operation at or above the Maximum Ratings values may impact device reliability or cause permanent damage to the device.

Information in this document is believed to be accurate and reliable. IXYSRF reserves the right to make changes to information published in this document at any time and without notice.

For detailed device mounting and installation instructions, see the "Device Installation & Mounting Instructions" technical note on the IXYSRF web site at;

[http://www.ixysrf.com/pdf/switch\\_mode/appnotes/7de\\_series\\_mosfet\\_installation\\_instructions.pdf](http://www.ixysrf.com/pdf/switch_mode/appnotes/7de_series_mosfet_installation_instructions.pdf)

IXYS RF reserves the right to change limits, test conditions and dimensions.

IXYS RF MOSFETS are covered by one or more of the following U.S. patents:

4,835,592	4,860,072	4,881,106	4,891,686	4,931,844	5,017,508
5,034,796	5,049,961	5,063,307	5,187,117	5,237,481	5,486,715
5,381,025	5,640,045				

Fig. 1 **Typical Transfer Characteristics**  
 $V_{DS} = 50V, I_D = 12A$

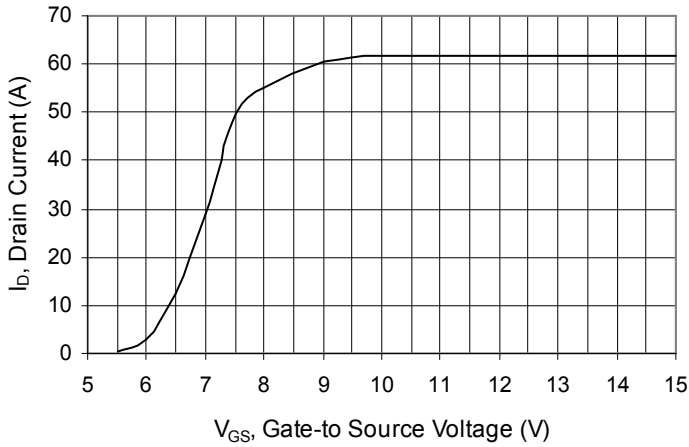


Fig. 2 **Typical Output Characteristics**  
 $PW = 15 \mu S$

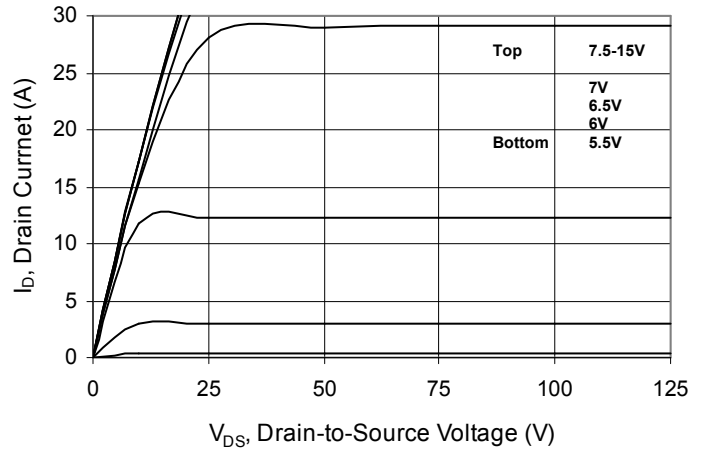


Fig. 3 **Gate Charge vs. Gate-to-Source Voltage**  
 $V_{DS} = 500V, I_D = 12A$

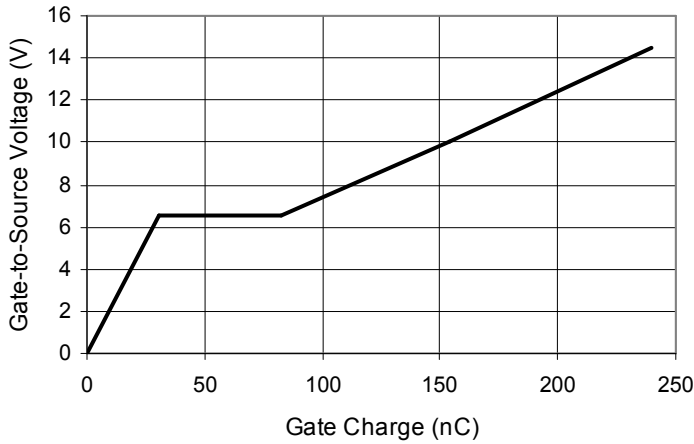


Fig. 4 **Extended Typical Output Characteristics**  
 $PW = 15 \mu S$

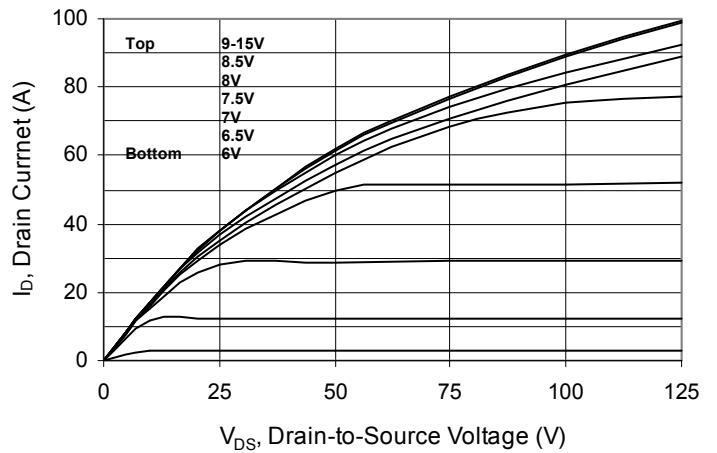


Fig. 5  **$V_{DS}$  vs. Capacitance**

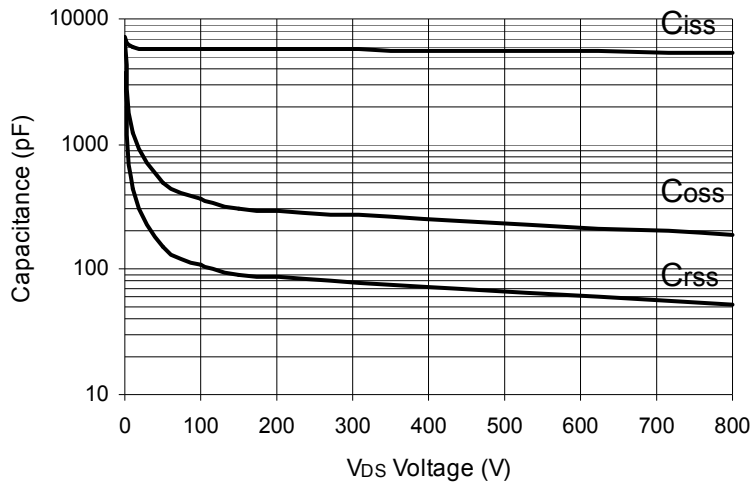


Fig. 6 Package Drawing

